

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A semiconductor device, comprising:
a mounting substrate having a first main surface and a second main surface opposite the first main surface;
a step portion formed in a periphery of the first main surface of the mounting substrate thereof;
a first conductive pattern formed on [[a]] the first main surface of the mounting substrate located inside the step portion;
a second conductive pattern formed on the second main surface of the mounting substrate;
a semiconductor element fixed to the first main surface of the mounting substrate and electrically connected to the first conductive pattern; and
sealing resin covering the first main surface of the mounting substrate and the step portion to seal the semiconductor element,
wherein a side surface of the sealing resin and a side surface of the mounting substrate are located on a same plane.

2. (Currently Amended) The semiconductor device according to claim 1, wherein the first conductive pattern comprises a bonding pad electrically connected to the semiconductor element through a fine metallic wire and a plating line extending from the bonding pad to the step portion.

3. (Original) The semiconductor device according to claim 2, wherein a plurality of the bonding pads are arranged so as to surround the semiconductor element, further comprising a wiring portion extending from each of the plurality of bonding pads under the semiconductor element.

4. (Withdrawn) A method of manufacturing a semiconductor device, comprising:
forming first conductive patterns which constitute units and common plating lines on a front surface of a substrate, each of the units comprising bonding pads and plating lines extending from the respective bonding pads to a periphery, the common plating lines electrically connecting the plating lines of the units;
forming second conductive patterns on a back surface of the substrate, the second conductive patterns being electrically connected to the respective first conductive patterns;
forming a plated film to a surface of the first conductive patterns by electroplating using the common plating lines;
forming grooves on the front surface of the substrate by dicing the front surface of the substrate including the common plating lines to electrically separate the conductive patterns;
placing semiconductor elements on the front surface of the substrate;
providing sealing resin which fills the grooves and seals the semiconductor elements; and
separating the semiconductor elements by dicing the substrate and the sealing resin at borders of the units.

5. (Withdrawn) The method of manufacturing a semiconductor device according to claim 4, wherein the units are arranged in a matrix, and the common plating lines extend along the borders of the units into a grid.

6. (New) The semiconductor device according to claim 1 wherein the mounting substrate comprises a resin.

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7. (New) The semiconductor device according to claim 1 wherein the second conductive pattern comprises electrodes arranged in a matrix.